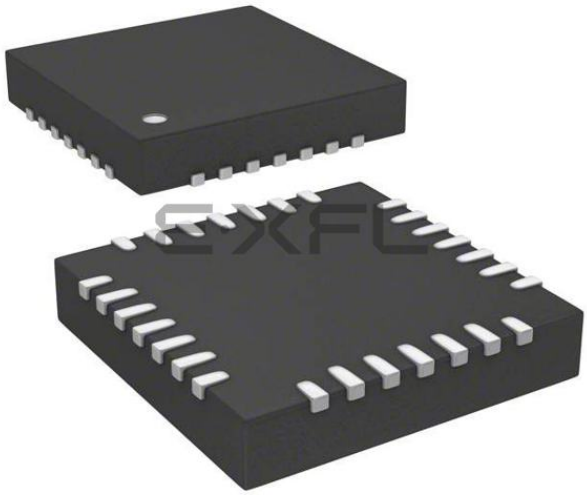


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	21
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l031g6u6

1 Introduction

The ultra-low-power STM32L031x4/6 family includes devices in 5 different package types from 20 to 48 pins. The description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L031x4/6 microcontrollers suitable for a wide range of applications:

- Gas/water meters and industrial sensors
- Healthcare and fitness equipment
- Remote control and user interface
- PC peripherals, gaming, GPS equipment
- Alarm system, wired and wireless sensors, video intercom

This STM32L031x4/6 datasheet should be read in conjunction with the STM32L0x1 reference manual (RM0377).

For information on the ARM® Cortex®-M0+ core please refer to the Cortex®-M0+ Technical Reference Manual, available from the www.arm.com website.

Figure 1 shows the general block diagram of the device family.

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to ARM® Cortex®-M4, including ARM® Cortex®-M3 and ARM® Cortex®-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 Ultra-low-power series are the best solution for applications such as gas/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.

Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
Consumption V_{DD}=1.8 to 3.6 V (Typ)	Down to 115 µA/MHz (from Flash)	Down to 25 µA/MHz (from Flash)	Down to 6.5 µA	Down to 3.2 µA	0.35 µA (No RTC) V_{DD}=1.8 V		0.23 µA (No RTC) V_{DD}=1.8 V	
					0.6 µA (with RTC) V_{DD}=1.8 V		0.39 µA (with RTC) V_{DD}=1.8 V	
					0.38 µA (No RTC) V_{DD}=3.0 V		0.26 µA (No RTC) V_{DD}=3.0 V	
					0.8 µA (with RTC) V_{DD}=3.0 V		0.57 µA (with RTC) V_{DD}=3.0 V	

1. Legend:
   "Y" = Yes (enable).
   "O" = Optional, can be enabled/disabled by software)
   "-" = Not available
2. Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
3. UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start.To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.
4. I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.

3.2 Interconnect matrix

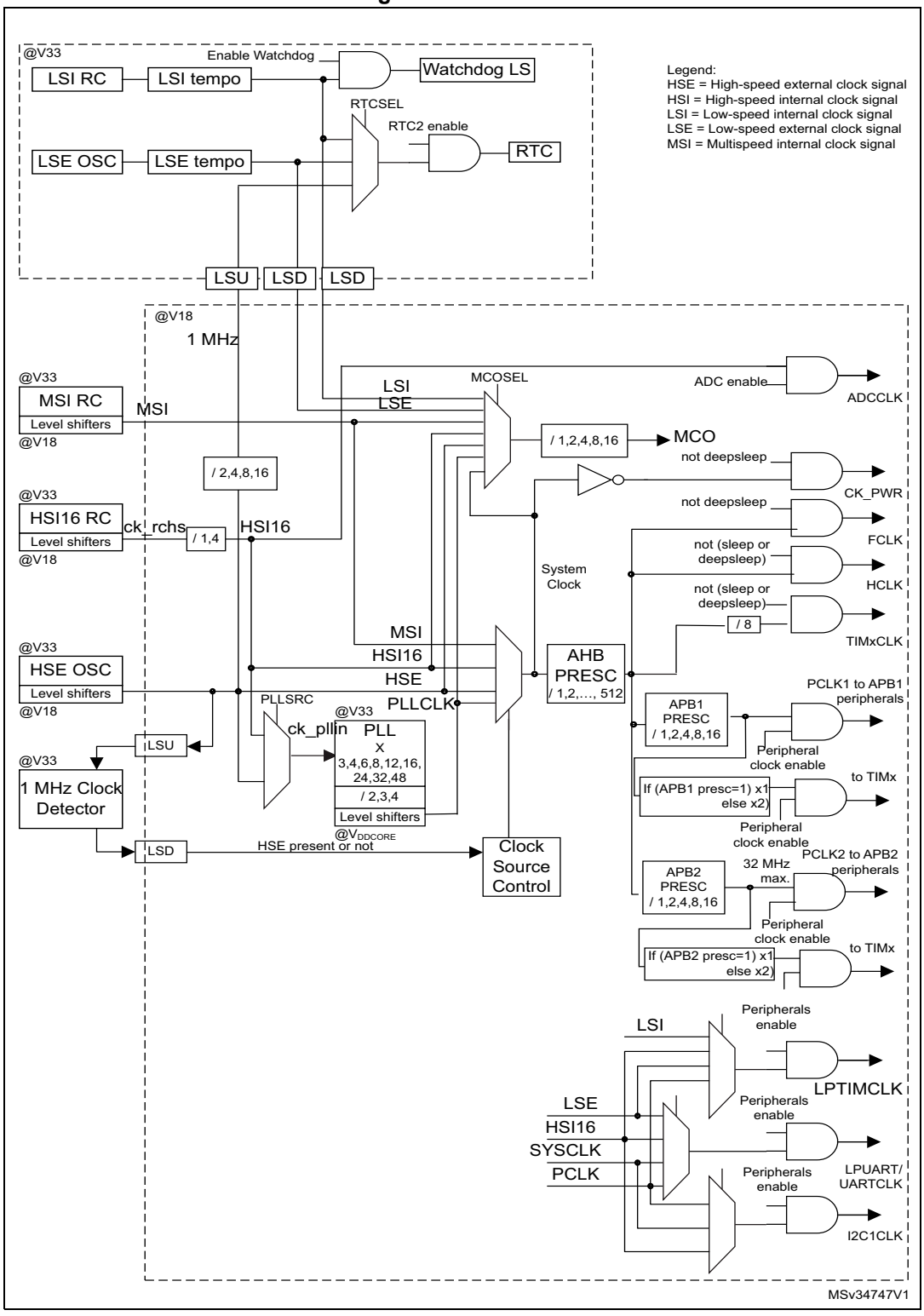
Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Table 6. STM32L0xx peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop
COMPx	TIM2,TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
	LPTIM	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	Y
TIMx	TIMx	Timer triggered by other timer	Y	Y	Y	Y	-

Figure 2. Clock tree



The ADC can be served by the DMA controller. It can operate from a supply voltage down to 1.65 V.

The ADC features a hardware oversampler up to 256 samples, this improves the resolution to 16 bits (see AN2668).

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers.

3.11 Temperature sensor

The temperature sensor (T_{SENSE}) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN18 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 7. Temperature sensor calibration values

Calibration value name	Description	Memory address
TSENSE_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3 V	0x1FF8 007A - 0x1FF8 007B
TSENSE_CAL2	TS ADC raw data acquired at temperature of 130 °C, V_{DDA}= 3 V	0x1FF8 007E - 0x1FF8 007F

3.11.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (since no external voltage, V_{REF+}, is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 8. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V_{DDA} = 3 V	0x1FF8 0078 - 0x1FF8 0079

Table 11. STM32L031x4/6 I²C implementation

I2C features(1)	I2C1
7-bit addressing mode	X
10-bit addressing mode	X
Standard mode (up to 100 kbit/s)	X
Fast mode (up to 400 kbit/s)	X
Fast Mode Plus with 20 mA output drive I/Os (up to 1 Mbit/s)	X(2)
Independent clock	X
SMBus	X
Wakeup from STOP	X

1. X = supported.
2. See *Table 15: Pin definitions on page 38* for the list of I/Os that feature Fast Mode Plus capability

3.15.2 Universal synchronous/asynchronous receiver transmitter (USART)

The USART interface (USART2) is able to communicate at speeds of up to 4 Mbit/s.

it provides hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART2 also supports Smartcard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability, auto baud rate feature and has a clock domain independent from the CPU clock that allows to wake up the MCU from Stop mode using baudrates up to 42 Kbaud.

USART2 interface can be served by the DMA controller.

Table 12 for the supported modes and features of USART interface.

Table 12. USART implementation

USART modes/features(1)	USART2
Hardware flow control for modem	X
Continuous communication using DMA	X
Multiprocessor communication	X
Synchronous mode(2)	X
Smartcard mode	X
Single-wire half-duplex communication	X
IrDA SIR ENDEC block	X
LIN mode	X
Dual clock domain and wakeup from Stop mode	X
Receiver timeout interrupt	X
Modbus communication	X
Auto baud rate detection (4 modes)	X
Driver Enable	X

1. X = supported.

Table 15. Pin definitions

Pin Number							Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
TSSOP20	WLCSP25[1]	UFQFPN28	UFQFPN28 (STM32L031GxUxS only)	LQFP32	UFQFPN32[2]	LQFP48						
-	-	-	-	-	-	2	PC13-ANTI_TAMP	I/O	FT	-	-	TAMP1/WKUP2
2	B5	2	2	2	2	3	PC14-OSC32_IN	I/O	TC	-	-	OSC32_IN
3	C5	3	3	3	3	4	PC15-OSC32_OUT	I/O	TC	-	-	OSC32_OUT
-	-	-	-	-	-	5	PH0-OSC_IN	I/O	TC	-	-	-
-	-	-	-	-	-	6	PH1-OSC_OUT	I/O	TC	-	-	-
4	D5	4	4	4	4	7	NRST	I/O	-	-	-	-
-	-	-	-	-	-	1	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT, LPUART1_RX	-
-	E1	-	-	-	"0"	8	VSSA	S	-	-	-	-
5	C4	5	5	5	5	9	VDDA	S	-	-	-	-
6	E5	6	6	6	6	-	PA0-CK_IN	I/O	TC	-	LPTIM1_IN1, TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1
-	-	-	-	-	-	10	PA0	I/O	TC	-	LPTIM1_IN1, TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1

Table 15. Pin definitions (continued)

Pin Number							Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
TSSOP20	WLCSP25[1]	UFQFPN28	UFQFPN28 (STM32L031GxUxS only)	LQFP32	UFQFPN32[2]	LQFP48						
1	A5	27	1	31	31	44	BOOT0	I	-	-	-	-
-	-	-	-	-	32	45	PB8	I/O	FTf	-	I2C1_SCL	-
-	-	-	-	-	-	46	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA	-
-	-	28	-	32	-	47	VSS	S	-	-	-	-
-	-	1	-	1	1	48	VDD	S	-	-	-	-

1. WLCSP25 package is in development. Its ballout is subject to change.
2. VSS pins are connected to the exposed pad (see *Figure 40: UFQFPN32, 5 x 5 mm, 32-pin package outline*).

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V ≤ V_{DD} ≤ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.

Figure 11. Pin loading conditions

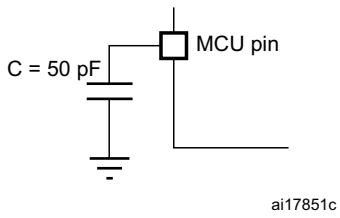
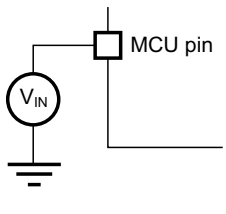
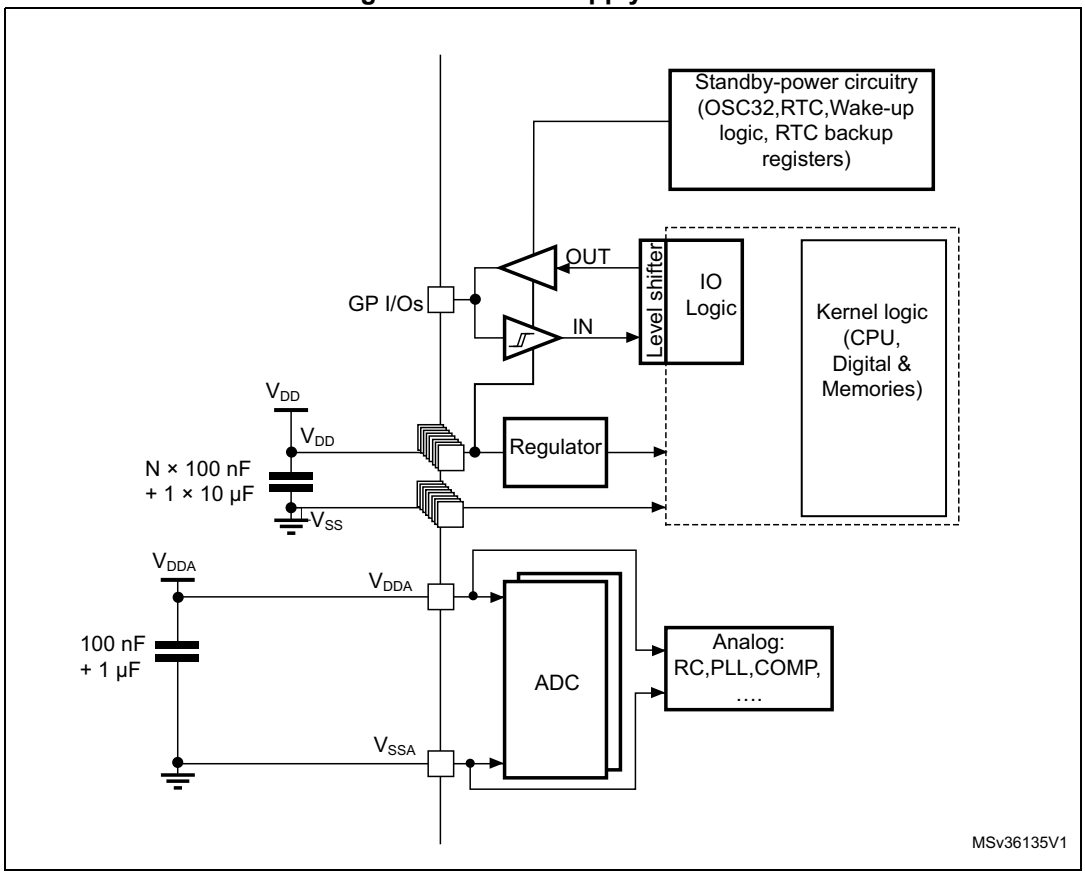


Figure 12. Pin input voltage



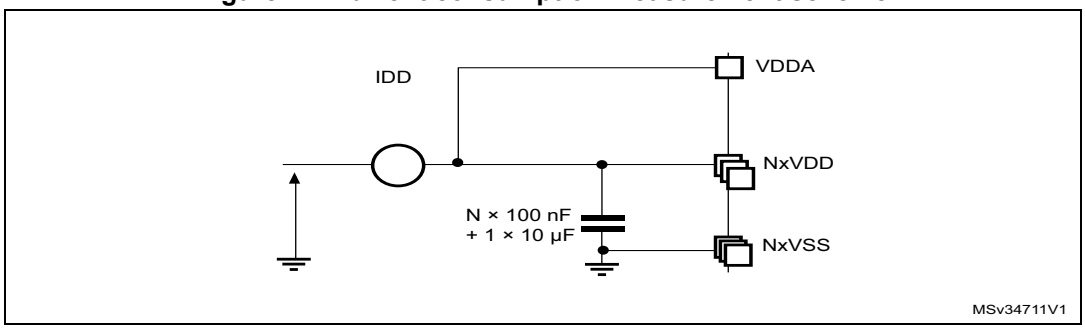
6.1.6 Power supply scheme

Figure 13. Power supply scheme



6.1.7 Current consumption measurement

Figure 14. Current consumption measurement scheme



6.3.3 Embedded internal reference voltage

The parameters given in *Table 23* are based on characterization results, unless otherwise specified.

Table 22. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C, V_{DDA}= 3 V	0x1FF8 0078 - 0x1FF8 0079

Table 23. Embedded internal reference voltage(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$(2)	Internal reference voltage	– 40 °C < T_J < +125 °C	1.202	1.224	1.242	V
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REFINT} value(3)	Including uncertainties due to ADC and V_{DDA} values	-	-	±5	mV
T_{Coeff}(4)	Temperature coefficient	–40 °C < T_J < +125 °C	-	25	100	ppm/°C
A_{Coeff}(4)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$(4)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$(4)(5)	ADC sampling time when reading the internal reference voltage	-	5	10	-	µs
T_{ADC_BUF}(4)	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I_{BUF_ADC}(4)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I_{VREF_OUT}(4)	VREF_OUT output current(6)	-	-	-	1	µA
C_{VREF_OUT}(4)	VREF_OUT output load	-	-	-	50	pF
I_{LPBUF}(4)	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V_{REFINT_DIV1}(4)	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}(4)	1/2 reference voltage	-	49	50	51	
V_{REFINT_DIV3}(4)	3/4 reference voltage	-	74	75	76	

1. Refer to *Table 35: Peripheral current consumption in Stop and Standby mode* for the value of the internal reference current consumption (I_{REFINT}).
2. Guaranteed by test in production.
3. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
4. Guaranteed by design.
5. Shortest sampling time can be determined in the application by multiple iterations.
6. To guarantee less than 1% VREF_OUT deviation.

Table 26. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched OFF	f_{HSE} = f_{HCLK} up to 16 MHz, included f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	115	170	µA
				2 MHz	210	250	
				4 MHz	385	420	
			Range 2, V_{CORE}=1.5 ,V, VOS[1:0]=10	4 MHz	0.48	0.6	mA
				8 MHz	0.935	1.1	
				16 MHz	1.8	2	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	1.1	1.3	
				16 MHz	2.1	2.3	
				32 MHz	4.5	4.7	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	22	52	µA
				524 kHz	70.5	91	
				4.2 MHz	420	450	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	1.95	2.2	mA
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	4.7	5.1	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 27. Current consumption in Run mode vs code type, code with data processing running from RAM(1)

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched OFF	f_{HSE} = f_{HCLK} up to 16 MHz, included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	385	µA
				CoreMark		395	
				Fibonacci		360	
				while(1)		265	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	4.5	mA
				CoreMark		4.65	
				Fibonacci		4.2	
				while(1)		3.05	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 28. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash memory OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	36.5	87	µA
				2 MHz	58	100	
				4 MHz	100	170	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	4 MHz	125	190	
				8 MHz	230	310	
				16 MHz	450	540	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	275	360	
				16 MHz	555	650	
				32 MHz	1350	1600	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	585	690	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	17	43	
				524 kHz	28	55	
				4.2 MHz	115	190	
	Supply current in Sleep mode, Flash memory ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	49	160	
				2 MHz	69	190	
				4 MHz	115	230	
			Range 2, $_{CORE}$=1.5 V, VOS[1:0]=10	4 MHz	135	200	
				8 MHz	240	320	
				16 MHz	460	550	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	290	370	
				16 MHz	565	670	
				32 MHz	1350	1600	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	600	700	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	28	55	
				524 kHz	39.5	67	
				4.2 MHz	125	200	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 29. Current consumption in Low-power run mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
I_{DD} (LP Run)	Supply current in Low-power run mode	All peripherals off, code executed from RAM, Flash memory OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	6.3	8.4	µA
				T_A = 85 °C	9.15	13	
				T_A = 105 °C	12.5	19	
				T_A = 125 °C	20.5	36	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A =-40 °C to 25 °C	9.45	12	
				T_A = 85 °C	12.5	15	
				T_A = 105 °C	16	22	
				T_A = 125 °C	24	38	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	17	20	
				T_A = 55 °C	19	21	
				T_A = 85 °C	20.5	24	
				T_A = 105 °C	23.5	28	
				T_A = 125 °C	31.5	46	
		All peripherals off, code executed from Flash memory, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	18.5	23	
				T_A = 85 °C	23	27	
				T_A = 105 °C	27	33	
				T_A = 125 °C	36	52	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	22.5	26	
				T_A = 85 °C	27.5	31	
				T_A = 105 °C	31	38	
				T_A = 125 °C	40.5	56	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	32	36	
				T_A = 55 °C	35	37	
				T_A = 85 °C	37.5	42	
				T_A = 105 °C	41	47	
				T_A = 125 °C	50	65	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

Table 36. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUSLEEP}$	Wakeup from Sleep mode	f_{HCLK} = 32 MHz	7	8	Number of clock cycles
$t_{WUSLEEP\_LP}$	Wakeup from Low-power sleep mode, f_{HCLK} = 262 kHz	f_{HCLK} = 262 kHz Flash memory enabled	7	8	
		f_{HCLK} = 262 kHz Flash memory switched OFF	9	10	
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI}$ = 4.2 MHz	5.0	8	µs
		$f_{HCLK} = f_{HSI}$ = 16 MHz	4.9	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	8.0	11	
	Wakeup from Stop mode, regulator in low-power mode	$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 1	5.0	8	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 2	5.0	8	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 3	5.0	8	
		$f_{HCLK} = f_{MSI}$ = 2.1 MHz	7.3	13	
		$f_{HCLK} = f_{MSI}$ = 1.05 MHz	13	23	
		$f_{HCLK} = f_{MSI}$ = 524 kHz	28	38	
		$f_{HCLK} = f_{MSI}$ = 262 kHz	51	65	
		$f_{HCLK} = f_{MSI}$ = 131 kHz	100	120	
		f_{HCLK} = MSI = 65 kHz	200	260	
		$f_{HCLK} = f_{HSI}$ = 16 MHz	4.9	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	8.0	11	
	Wakeup from Stop mode, regulator in low-power mode, code running from RAM	$f_{HCLK} = f_{HSI}$ = 16 MHz	4.9	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	7.9	10	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz	4.7	8	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	f_{HCLK} = MSI = 2.1 MHz	65	130	
	Wakeup from Standby mode FWU bit = 0	f_{HCLK} = MSI = 2.1 MHz	2.2	3	ms

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.The external clock signal has to respect the I/O characteristics in *Section 6.3.12*. However, the recommended clock input waveform is shown in *Figure 20*.

Table 37. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	CSS is on or PLL is used	1	8	32	MHz
		CSS is off, PLL not used	0	8	32	MHz
V_{HSEH}	OSC_IN/CK_IN(2) input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN/CK_IN(2) input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN/CK_IN(2) high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN/CK_IN(2) rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN/CK_IN(2) input capacitance		-	2.6	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	OSC_IN/CK_IN(2) Input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$	-	-	±1	µA

1. Guaranteed by design.
2. HSE external user clock is applied to OSC_IN on LQFP48 package and to CK_IN on other packages.

Figure 20. High-speed external clock source AC timing diagram

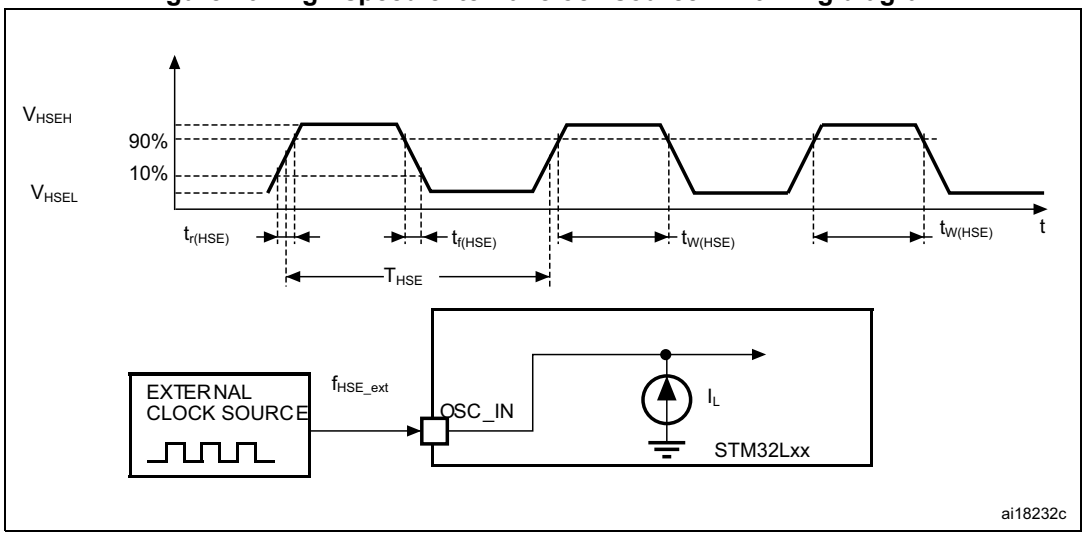


Table 43. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{SU(MSI)}$	MSI oscillator startup time	MSI range 0	30	-	µs
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
		MSI range 4	6	-	
		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
$t_{STAB(MSI)}$(2)	MSI oscillator stabilization time	MSI range 0	-	40	µs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{OVER(MSI)}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Guaranteed by characterization results.

6.3.8 PLL characteristics

The parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Table 44. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max(1)	
f_{PLL_IN}	PLL input clock(2)	2	-	24	MHz
	PLL input clock duty cycle	45	-	55	%

Figure 25. V_{IH}/V_{IL} versus VDD (CMOS I/Os)

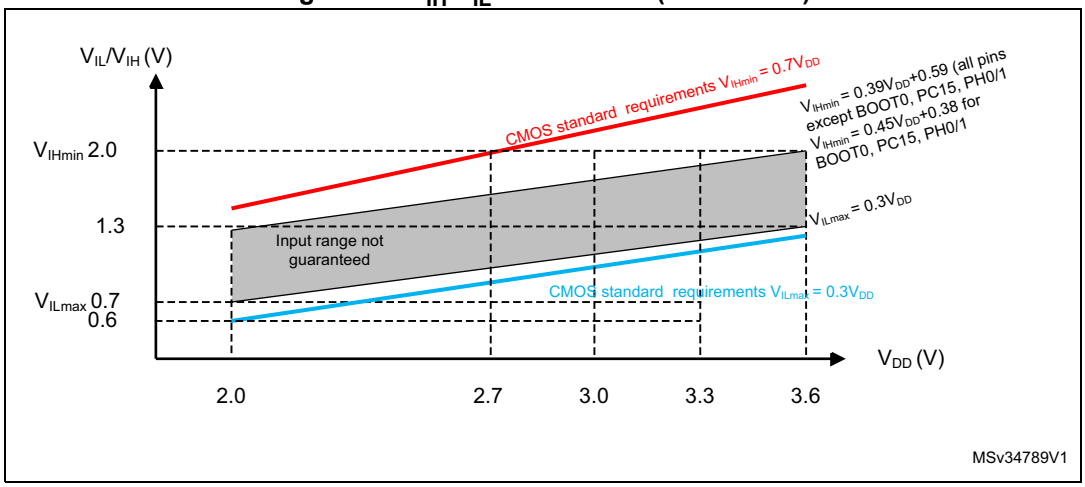
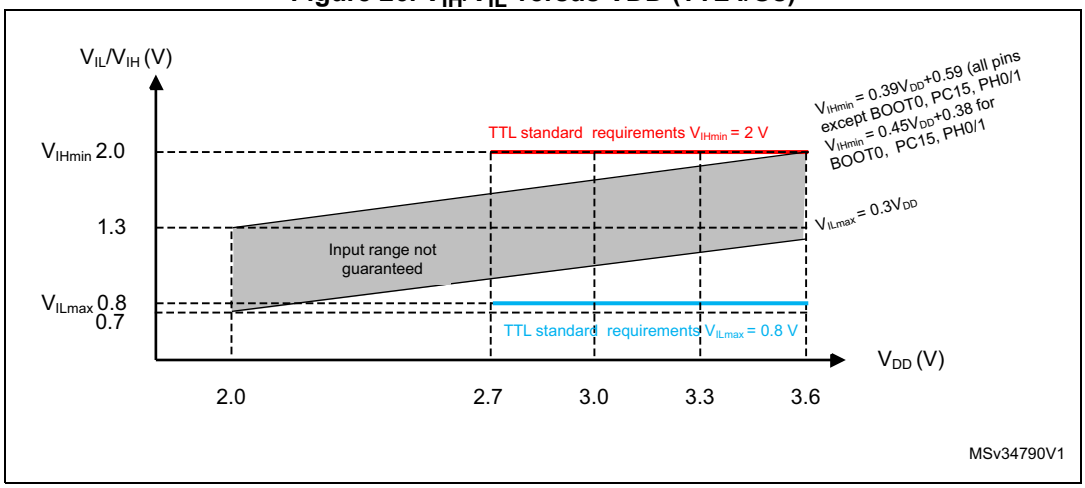


Figure 26. V_{IH}/V_{IL} versus VDD (TTL I/Os)



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±15 mA with the non-standard V_{OL}/V_{OH} specifications given in *Table 54*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating $I_{VDD(\Sigma)}$ (see *Table 18*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating $I_{VSS(\Sigma)}$ (see *Table 18*).

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 27* and *Table 55*, respectively.

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Table 55. I/O AC characteristics(1)

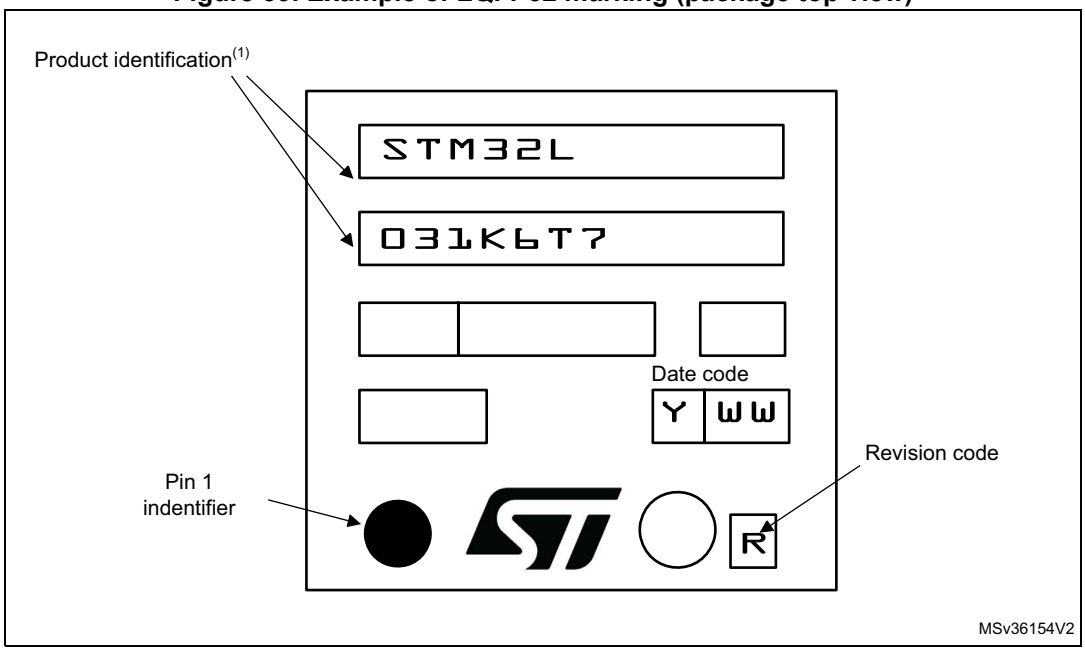
OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	
Fm+ configuration(4)	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.5 V to 3.6 V	-	1	MHz
	$t_{f(IO)out}$	Output fall time		-	10	ns
	$t_{r(IO)out}$	Output rise time		-	30	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 1.65 V to 3.6 V	-	350	KHz
	$t_{f(IO)out}$	Output fall time		-	15	ns
	$t_{r(IO)out}$	Output rise time		-	60	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in *Figure 27*.
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

LQFP32 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Figure 39. Example of LQFP32 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.